

**CENTRE FOR MATERIALS FOR ELECTRONICS TECHNOLOGY (C-MET)**

(Scientific Society, Ministry of Electronics and Information Technology (MeitY), Govt. of India)

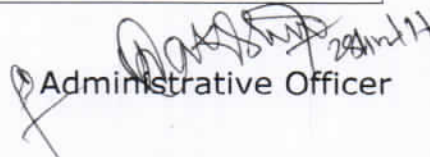
IDA PHASE – III, CHERLAPALLY, HCL (PO), HYDERABAD – 500 051

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TERMS AND CONDITIONS

1. The specifications for the items quoted should be explicit, clear and all available technical literature, catalogues and other data in support of the specifications of the items should be furnished along with the quotation.
2. Quotation should be valid for a minimum period of NINETY DAYS from the due date.
3. The sealed quotation should reach on or before the specified date to the Administrative Officer, Centre for Materials for Electronics Technology, IDA Phase-III, Cherlapally, HCL (PO), Hyderabad –500 051.
4. It should be mentioned specifically whether the price quoted includes all taxes and duties. Sales tax and / or other duties and levies where legally leviable and intended to be claimed should be distinctly shown separately in the tender. VAT/CST registration No. and date up to its validity should be indicated. **We won't be able to provide "C" & "D" forms, hence quote for the taxes actually leviable.**
5. **We are exempted from Excise Duty and Customs Duty as per Notification No. 10/97-Central Excise dated 01.03.1997 & No. 16/2007-Central Excise dated 01.03.2007 AND No. 51/96-Customs dated 23.07.1996 & No. 24/2007-Customs dated 01.03.2007 respectively.**
6. C-MET takes no responsibility for delay, loss or non-receipt of quotations/documents sent by post and reserve the right to accept or reject any part of the tender without assigning any reasons.
7. Corrections if any must be attested. All rates shall be indicated both in words as well as in figures. Where there is a difference between rates quoted in words and figures, rate quoted in words will prevail.
8. Terms and Conditions for the contract to be signed for the supply of items should be provided along with the quotation.
9. Tenders should submit along with their quotation, details of similar equipments / machineries supplied to Scientific / Technical Institutions during the past 3 years in India and the reference to that effect may be clearly mentioned.
10. In case you are an Authorized Agent and can arrange supply of the items, please forward your quotation F.O.R. Destination Hyderabad only along with the authorization letter from the manufacture.
11. **CHECK LIST**
Please ensure to check the following before submitting quotation otherwise quotation will be liable for rejection:

1	Price	Verify price quoted both in figures and words are correct.
2	Validity of offer	Please indicate that Offer is valid for a period of 90 days from the date of opening of price bid.
3	Payment terms quoted *	100% after delivery & installation of the item. No advance/part payment will be effected. <u>* our normal mode of payment is 100% within 30 days after receipt and acceptance of materials in good condition (i.e. within 30 days after satisfactorily installation & commissioning).</u>
4	Delivery period	Should be clearly indicated. Delivery of the item within Time limit is the essence of the contract failure will attract Penalty.
5.	Packing & forwarding charges	Should be clearly indicated. Mentioning "EXTRA" will not be acceptable.
6	Payment of statutory levies	Central/VAT - Full CESS - Full Excise duty - Exempted Custom duty - Exempted
7	Freight charges	Clearly indicate delivery charges Paid or FREE up to CMET stores, Cherlapally, Hyderabad- 51.
8	Transit Insurance	Clearly indicate to be borne by the party or C-MET.
9.	Guarantee / Warrantee	Party should clearly indicate period of warrantee and after sales service/AMC


Administrative Officer

SPECIFICATIONS OF 6H N-SiC SINGLE CRYSTAL SUBSTRATE

Sl. No	SiC Wafer Properties	Specifications
1.	SiC wafer type (Polytype)	6H SiC
2.	Bandgap	3.0 eV
3.	Diameter	2" (inch)
4.	Quantity	40 no.
5.	Conductivity Type	N - type
6.	Substrate thickness	$\geq 325 \pm 25 \mu\text{m}$
7.	Packing	Single wafer
8.	Full Width Half Maxima (FWHM)	$< 30 \text{ arc-sec}$
9.	Micropipe density (MPD)	$< 10 \text{ cm}^{-2}$
10.	Orientation	Off axis : 3.5° towards $\langle 11-20 \rangle \pm 0.5^\circ$
11.	Surface finish	Double side polished:- a) One side:- C-face - CMP, Epi-ready (Preferred) b) Other side:- Si-face - optical polish / CMP
12.	Surface Roughness	$R_a < 2 \text{ nm}$
13.	Resistivity	$> 0.05 \text{ Ohm-cm}$



**SPECIFICATIONS OF SEMI-INSULATING SI 6H SiC SINGLE
CRYSTAL SUBSTRATE**

Sl. No	Sic Wafer Properties	Specifications
1.	SiC wafer type (Polytype)	Semi-insulating (SI) 6H SiC
2.	Bandgap	3.0 eV
3.	Diameter	2" (inch)
4.	Quantity	10 no.
5.	Conductivity Type	SI - type
6.	Substrate thickness	$\geq 325 \pm 25 \mu\text{m}$
7.	Packing	Single wafer
8.	Full Width Half Maxima (FWHM)	< 30 arc-sec
9.	Micropipe density (MPD)	< 10 cm^{-2}
10.	Orientation	Off axis : 3.5° towards $\langle 11-20 \rangle \pm 0.5^\circ$ / On-axis: $\langle 0001 \rangle \pm 0.5^\circ$
11.	Surface finish	Double side polished:- a) One side:- C-face - CMP, Epi-ready (Preferred) b) Other side:- Si-face - optical polish / CMP
12.	Surface Roughness	$R_a < 2 \text{ nm}$
13.	Resistivity	$> 1\text{E}5 \text{ Ohm-cm}$

